

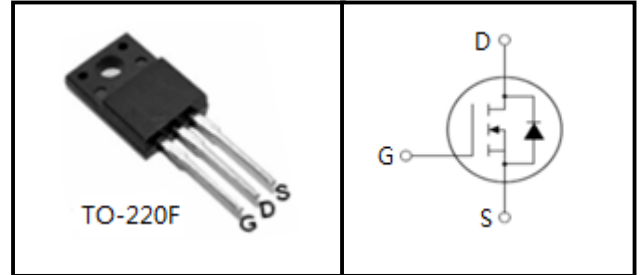
700V N-Channel MOSFET

FEATURES

- Fast switching
- 100% avalanche tested
- Improved dv/dt capability

APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)



Device Marking and Package Information

Device	Package	Marking
CS8N70F	TO-220F	CS8N70F

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	value	Unit
Drain-Source Voltage ($V_{GS} = 0V$)	V_{DSS}	700	V
Continuous Drain Current	I_D	8	A
Pulsed Drain Current (note1)	I_{DM}	32	A
Gate-Source Voltage	V_{GSS}	± 30	V
Single Pulse Avalanche Energy (note2)	E_{AS}	217.8	mJ
Avalanche Current (note1)	I_{AR}	6.6	A
Repetitive Avalanche Energy (note1)	E_{AR}	130.68	mJ
Power Dissipation ($T_C = 25^\circ\text{C}$)	P_D	65	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55~+150	$^\circ\text{C}$

Thermal Resistance

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	R_{thJC}	1.92	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Ambient	R_{thJA}	62.5	

Specifications $T_J = 25^{\circ}\text{C}$, unless otherwise noted

Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	700	--	--	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 700V, V _{GS} = 0V, T _J = 25°C	--	--	1	μA
Gate-Source Leakage	I _{GSS}	V _{GS} = ±30V	--	--	±100	nA
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	3.0	--	4.0	V
Drain-Source On-Resistance (Note3)	R _{DS(on)}	V _{GS} = 10V, I _D = 4A	--	0.95	1.1	Ω
Dynamic						
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = 25V, f = 1.0MHz	--	1197	--	pF
Output Capacitance	C _{oss}		--	113	--	
Reverse Transfer Capacitance	C _{rss}		--	15	--	
Total Gate Charge	Q _g	V _{DD} = 560V, I _D = 8A, V _{GS} = 10V	--	37	--	nC
Gate-Source Charge	Q _{gs}		--	5.5	--	
Gate-Drain Charge	Q _{gd}		--	19	--	
Turn-on Delay Time	t _{d(on)}	V _{DD} = 350V, I _D =8A, R _G = 25 Ω	--	43	--	ns
Turn-on Rise Time	t _r		--	30	--	
Turn-off Delay Time	t _{d(off)}		--	145	--	
Turn-off Fall Time	t _f		--	67.5	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I _S	T _C = 25 °C	--	--	8	A
Pulsed Diode Forward Current	I _{SM}		--	--	32	
Body Diode Voltage	V _{SD}	T _J = 25°C, I _{SD} = 4A, V _{GS} = 0V	--	--	1.4	V
Reverse Recovery Time	t _{rr}	V _{GS} = 0V, I _S = 8A, di _F /dt =100A /μs	--	612	--	ns
Reverse Recovery Charge	Q _{rr}		--	2.5	--	μC

Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. $L=10mH, V_{DD} = 50V, R_G = 25\Omega$, Starting $T_J = 25^{\circ}\text{C}$
3. Pulse Test: Pulse width $\leq 300\mu s$, Duty Cycle $\leq 1\%$

Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 1. Output Characteristics ($T_J = 25^\circ\text{C}$)

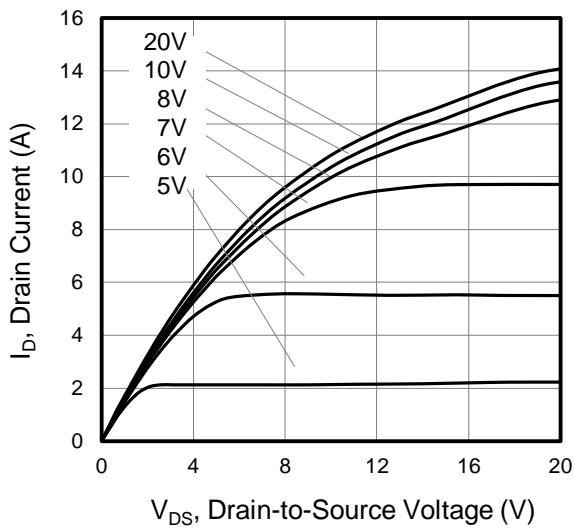


Figure 2. Body Diode Forward Voltage

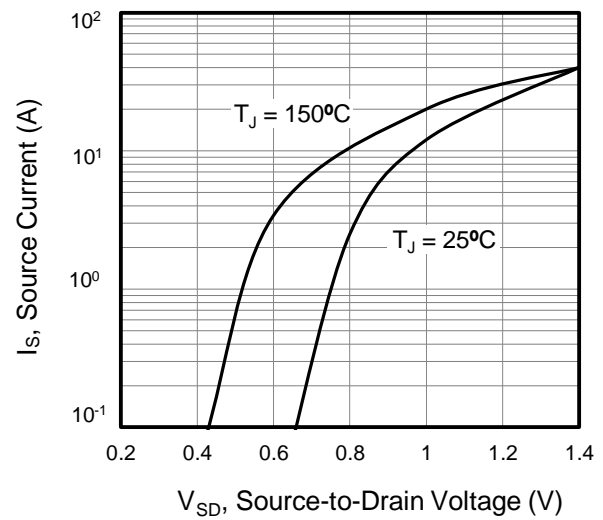


Figure 3. Drain Current vs. Temperature

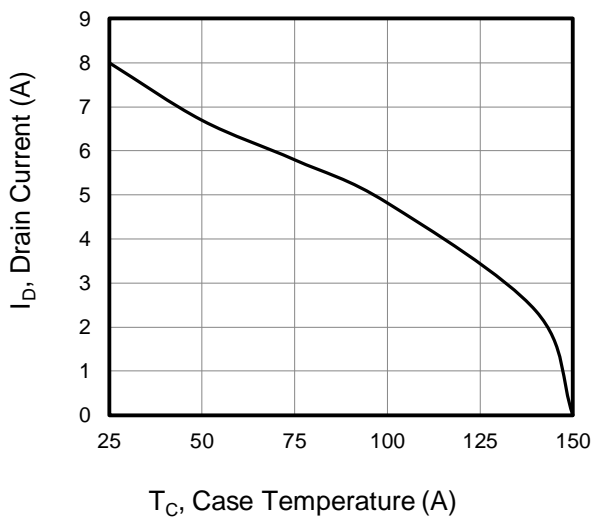


Figure 4. BV_{DSS} Variation vs. Temperature

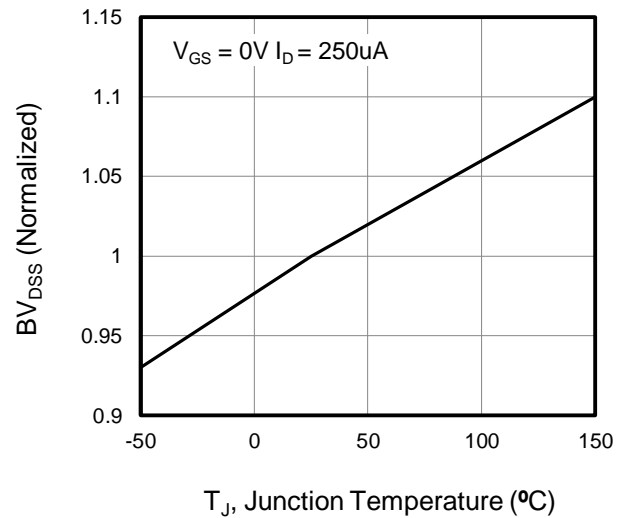


Figure 5. Transfer Characteristics

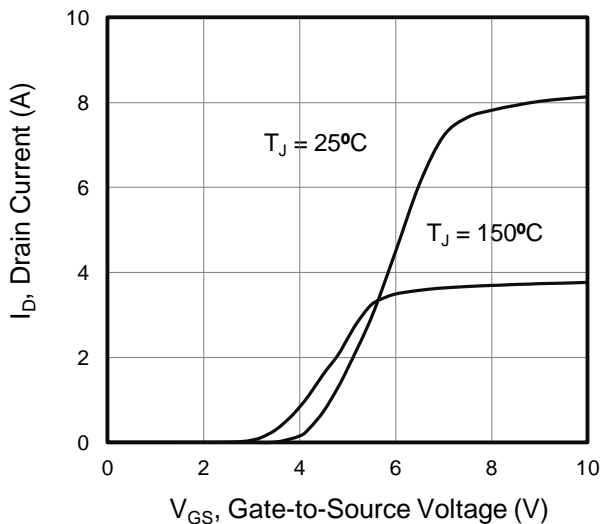
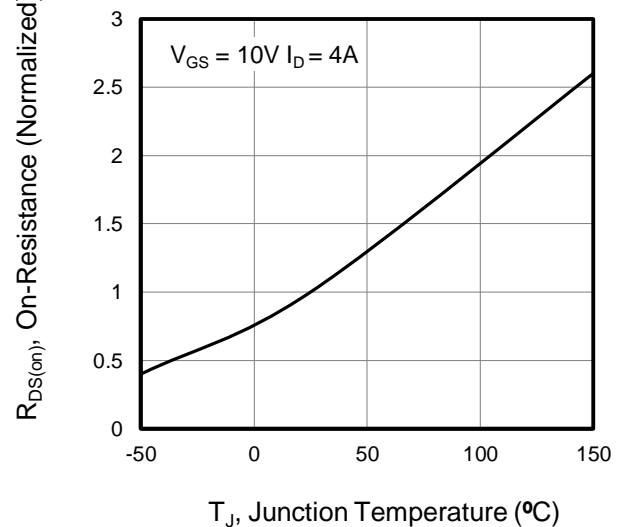


Figure 6. On-Resistance vs. Temperature



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 7. Capacitance

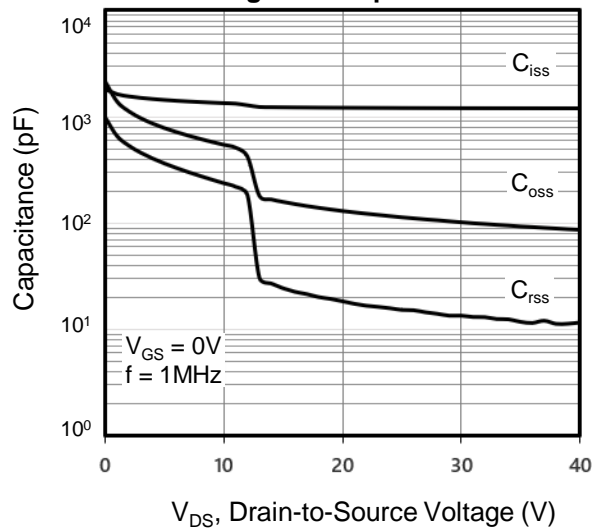


Figure 8. Gate Charge

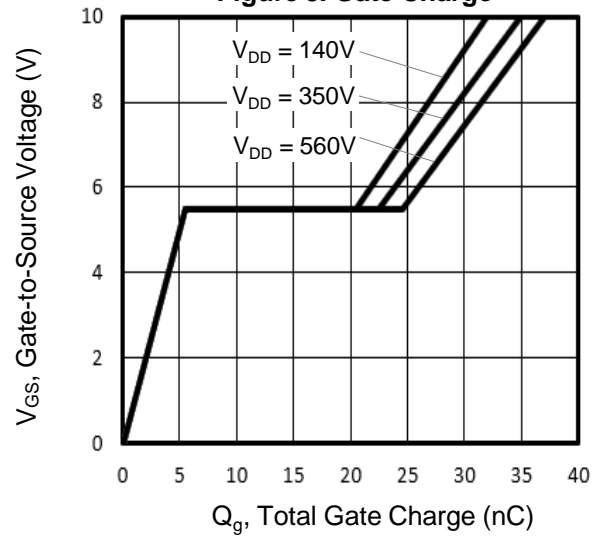


Figure 9. Transient Thermal Impedance

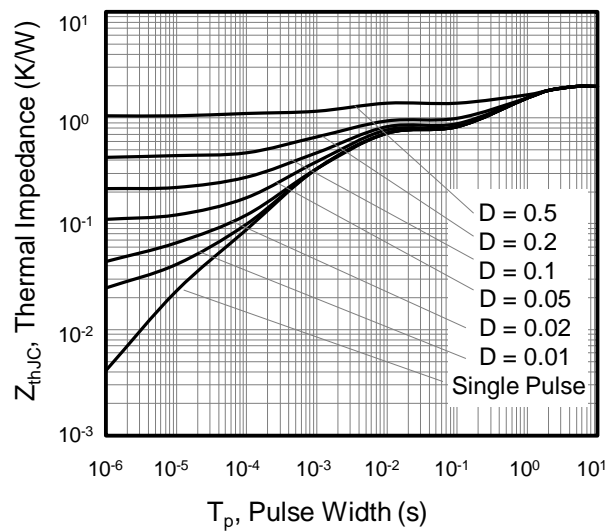
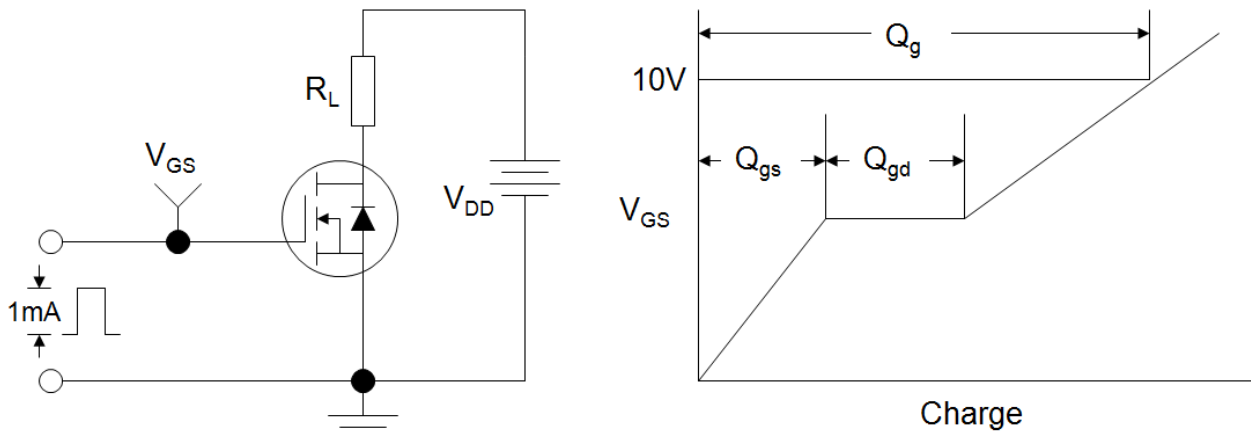
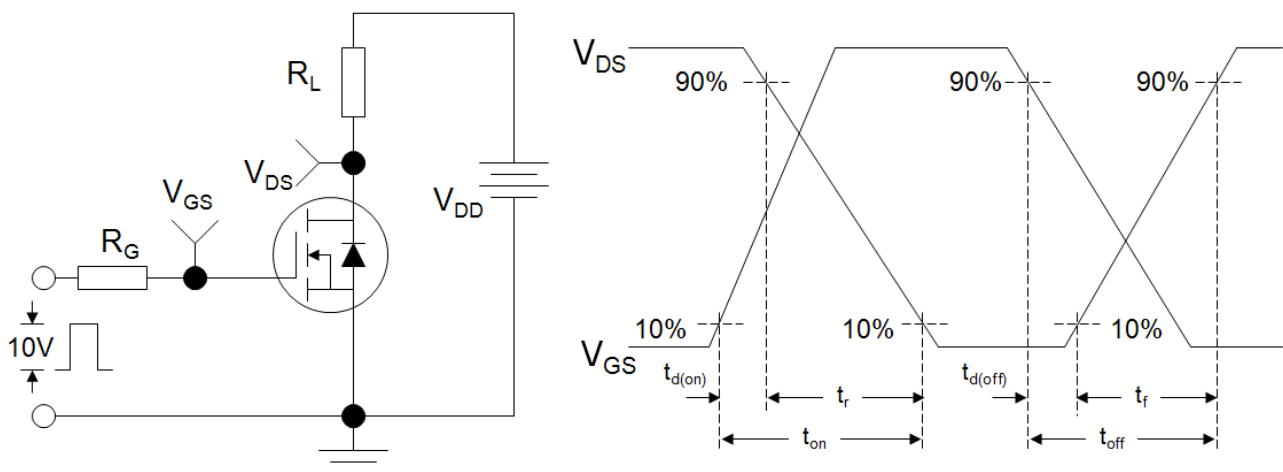
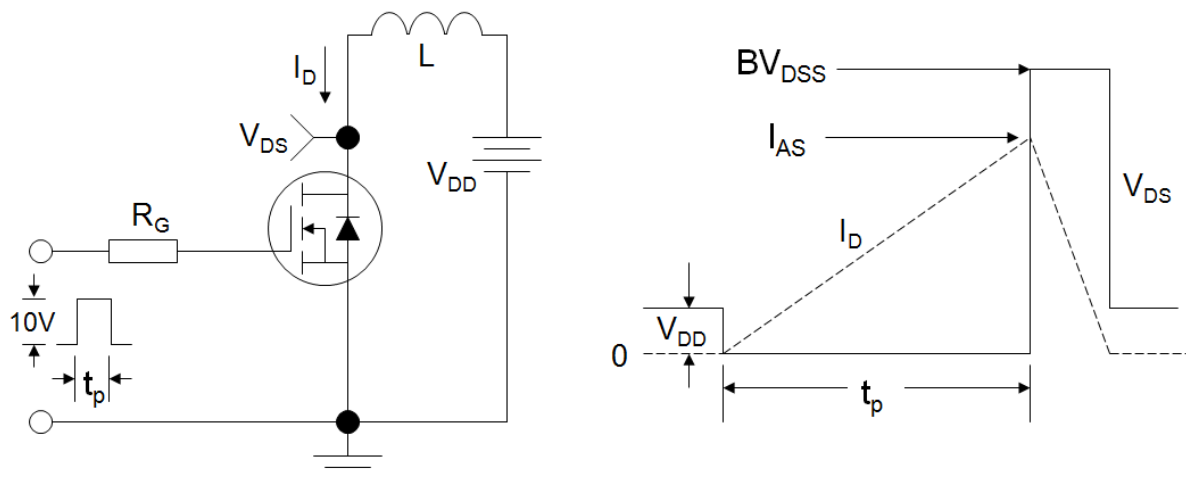
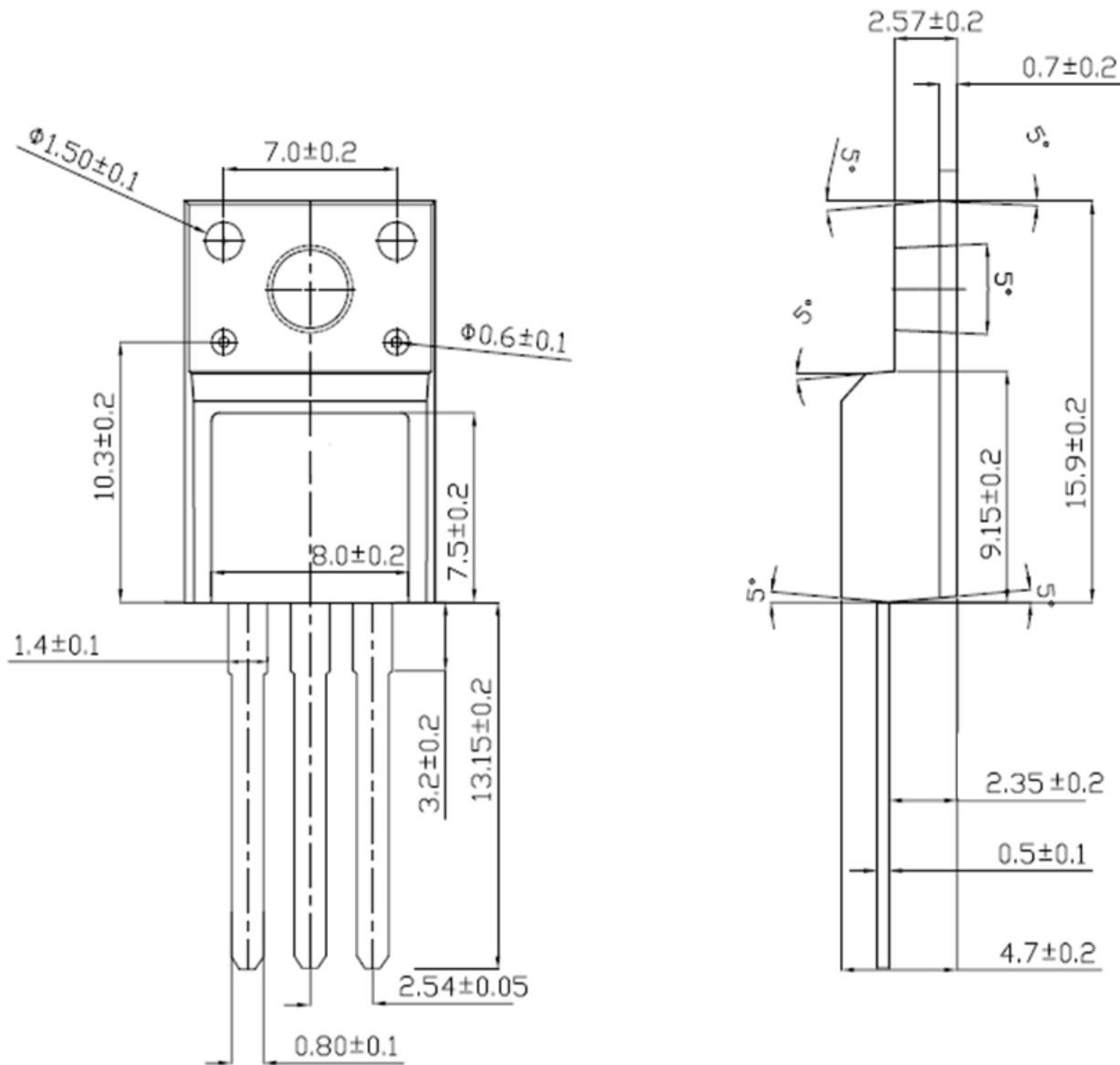


Figure A: Gate Charge Test Circuit and Waveform

Figure B: Resistive Switching Test Circuit and Waveform

Figure C: Unclamped Inductive Switching Test Circuit and Waveform


TO-220F



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